





### 31DQ04 SCHOTTKY RECTIFIER



#### Features

- Low profile, axial leaded outline
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	40	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>C</sub> =73°C, rectangular wave form On PC board 9mm² island	3.3	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse, T <sub>C</sub> = 25 °C	80	Α

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 3A, Pulse, T <sub>J</sub> = 25 °C	0.55	0.57	V
		@ 6 A, Pulse, T <sub>J</sub> = 25 °C	0.65	0.71	V
	$V_{F2}$	@ 3 A, Pulse, T <sub>J</sub> = 125 °C	0.48	0.51	V
		@ 6 A, Pulse, T <sub>J</sub> = 125 °C	0.60	0.62	V
Reverse Current*	I <sub>R1</sub>	$@V_R$ = Rated $V_R$ , Pulse, $T_J$ = 25 °C	0.1	1	mA
	$I_{R2}$	$@V_R = Rated V_R, Pulse, T_J = 125 °C$	7	20	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	130	190	PF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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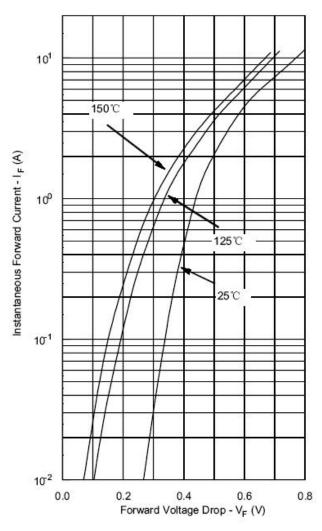


# **Thermal-Mechanical Specifications:**

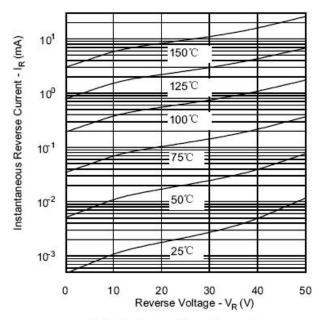
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-40 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-40 to +150	°C
Typical Thermal Resistance Junction to Ambient	R <sub>θ</sub> JA	-	80	°C/W
Typical Thermal Resistance Junction to Lead	R <sub>θJL</sub>	-	34	°C/W
Approximate Weight	wt	-	1.02	g

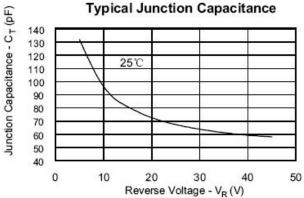
# **Ratings and Characteristics Curves**

#### **Typical Forward Characteristics**



#### Typical Reverse Characteristics





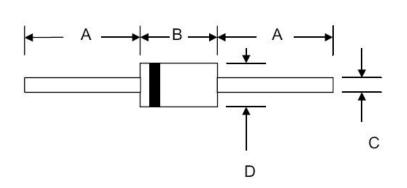
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### **Mechanical Dimensions DO-201AD**



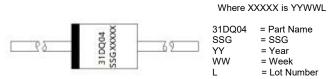
CVMPOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	25.4	-	1.000	-	
В	8.50	9.50	0.335	0.374	
С	1.2	1.3	0.048	0.052	
D	5.0	5.6	0.197	0.220	

## **Ordering Information**

Device	Package	Shipping	
31DQ04	DO-201AD (Pb-Free)	1250pcs /tape	
31DQ04TA	DO-201AD (Pb-Free)	1250pcs /tape	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

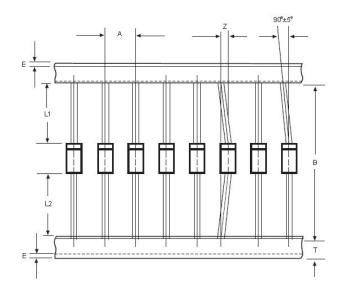
## **Marking Diagram**



Cautions: Molding resin

Epoxy resin UL:94V-0

### **Carrier Tape Specification DO-201AD**



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
А	9.50	10.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
E	-	0.80	
IL1-L2I	-	1.0	

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